

M66313FP

32-Bit LED Driver with Shift Register and Latch

REJ03F0179-0201 Rev.2.01 Mar 31, 2008

Description

The M66313FP is a semiconductor integrated circuit for LED array driver with 32-bit serial-input, parallel-output shift register, equipped with direct set input and output latches.

The M66313FP guarantees sufficient 24 mA output current to drive anode common LED, allowing 32-bit simultaneous and continuous current output.

The parallel outputs are open-drain outputs.

The M66313FP employs CMOS technology, allowing considerable reduction of power dissipation, compared to previous BIPOLAR or Bi-CMOS products.

In addition, the pin configuration is suitable for easy wiring on the printed circuit board.

Features

• High output current.

All parallel output $I_{OL} = +24$ mA, LEDs can be turned on simultaneously.

Low power dissipation : 200 μW/package (max)

 $(V_{CC} = 5 \text{ V}, \text{ Ta} = 25^{\circ}\text{C}, \text{ quiescent state})$

• High noise margin

Employment of Schmitt-trigger circuit on all inputs allows application with long wiring.

- Direct set input (\overline{S}_D)
- Open-drain output $(\overline{Q}_1 \text{ to } \overline{Q}_{32})$
- Serial data output for cascading (SQ₃₂)
- Wide operating temperature range ($Ta = -40 \text{ to } +85^{\circ}\text{C}$)
- Pin configuration for easy layout on PCB.
 (Pin configuration allows easy cascade connection or LED connection)

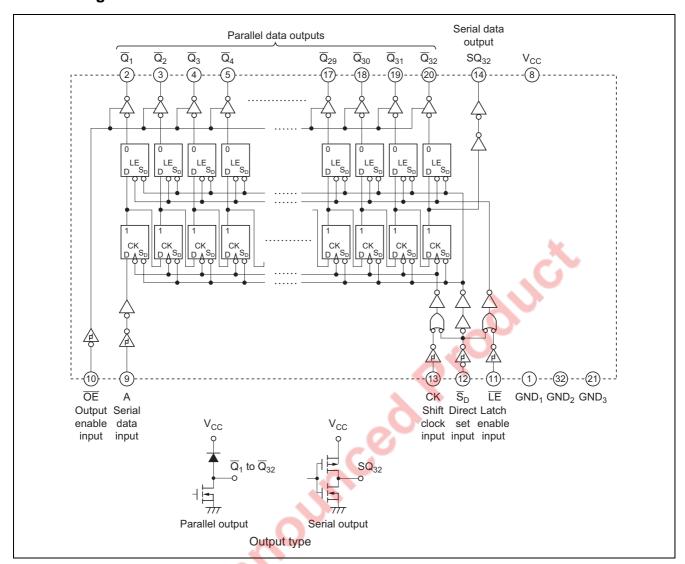
Application

LED array drive for eraser unit of a copying machine

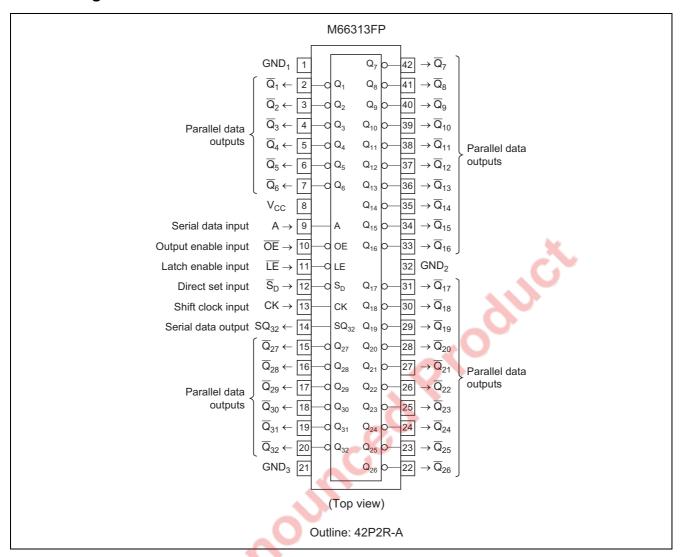
LED array drive of a button telephone set

Various LED modules

Block Diagram



Pin Arrangement



Functional Description

The employment of silicon gate CMOS process of the M66313FP guarantees low power dissipation and maintains high noise margin as well as high output current and high speed required to drive LEDs.

Each shift register bit consists of a flip-flop for shifting and an output latch.

The shift operation takes place when the clock input CK changes from low-level to high-level.

The serial data input A corresponds to the data input of the first-stage shift register, and the shift register is shifted in sequence when a pulse is applied to CK.

The parallel outputs \overline{Q}_1 to \overline{Q}_{32} are open-drain outputs.

If the latch-enable input \overline{LE} is turned high-level, the content of the shift register at that instant is latched.

To expand the number of bits, use the serial data output SQ₃₂ which shows the output of the shift register of the 32nd bit.

If the direct set input \overline{S}_D is turned low-level, shift register and latches are set.

If the high-level input is applied to the output enable input \overline{OE} , \overline{Q}_1 to \overline{Q}_{32} are set to the high-impedance state, but SQ_{32} is not set to the high-impedance state. The shift operation is not affected when \overline{OE} is changed.

Function Table (Note)

Operation		ı	npu	t															Pa	ralle	el D	ata (Out	put														Serial Data Output
Mode	$\overline{\mathbb{S}}_{\mathbb{D}}$	CK	ĪĒ	Α	ŌĒ	$\overline{\mathbb{Q}}_1$	\overline{Q}_2	\overline{Q}_3	$\overline{\mathbb{Q}}_4$	\overline{Q}_{5}	\overline{Q}_6	\overline{Q}_7	\overline{Q}_8	\overline{Q}_9	\overline{Q}_{10}	$\overline{\mathbb{Q}}_{11}$	\overline{Q}_{12}	\overline{Q}_{13}	\overline{Q}_{14}	\overline{Q}_{15}	\overline{Q}_{16}				$\overline{\mathbb{Q}}_{20}$	$\overline{\mathbb{Q}}_{21}$	\overline{Q}_{22}	\overline{Q}_{23}	\overline{Q}_{24}			\overline{Q}_{27}	\overline{Q}_{28}	\overline{Q}_{29}	\overline{Q}_{30}	\overline{Q}_{31}	\overline{Q}_{32}	SQ ₃₂
Set	L	Х	Х	Χ	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	Г	L	L	Н
Shift	Н	1	L	Н	L	L	$\overline{\mathbb{Q}}_{1}$	\overline{Q}^{0}_{2}	\overline{Q}_{3}	$\overline{Q}_{_{4}}^{_{0}}$	$\overline{Q}{}^{0}_{5}$	\overline{Q}_{6}^{0}	$\overline{\mathbb{Q}}_{7}$	\overline{Q}_{8}^{0}	\overline{Q}_{9}^{0}	$\overline{\mathbb{Q}}_{10}$	$\overline{\mathbb{Q}}_{11}$	$\overline{\mathbb{Q}}_{12}$	\overline{Q}^{0}_{13}	Q ₀	\overline{Q}_{15}	$\overline{Q}{}^{0}_{16}$	Q ₀₁₇	$\overline{Q}{}^{0}_{18}$	Q ₀₁₉	$\overline{Q}{}^{0}_{20}$	\overline{Q}^{0}_{21}	$\overline{Q}{}^{0}_{22}$	$\overline{Q}{}^{0}_{23}$	$\overline{Q}{}^{0}_{24}$	$\overline{Q}{}^{0}_{25}$	$\overline{Q}{}^{0}_{26}$	$\overline{Q}{}^{0}_{27}$	Q ₀₂₈	$\overline{Q}{}^{0}_{29}$	\overline{Q}_{30}	$\overline{Q}{}^{0}_{31}$	q ⁰ ₃₁
	Н	1	L	L	L	Z	$\overline{\mathbb{Q}}_{1}$	\overline{Q}_{2}^{0}	\overline{Q}_{3}	$\overline{Q}_{_{4}}^{_{0}}$	$\overline{Q}{}^{0}_{5}$	\overline{Q}_{6}^{0}	$\overline{\mathbb{Q}}_{7}$	\overline{Q}_{8}^{0}	\overline{Q}_{9}^{0}	$\overline{\mathbb{Q}}_{10}$	$\overline{\mathbb{Q}}_{11}$	$\overline{\mathbb{Q}}_{12}$	Q ₀ 13	Q ₀	$\overline{\mathbb{Q}}_{15}$	$\overline{Q}{}^{0}_{16}$	Q ₀₁₇	$\overline{Q}{}^{0}_{18}$	Q ₀₁₉	$\overline{Q}{}^{0}_{20}$	$\overline{\mathbb{Q}}_{21}$	$\overline{Q}{}^{0}_{22}$	$\overline{Q}{}^{0}_{23}$	$\overline{Q}{}^{0}_{24}$	$\overline{Q}{}^{0}_{25}$	$\overline{Q}{}^{0}_{26}$	$\overline{Q}{}^{0}_{27}$	Q ₀₂₈	$\overline{Q}{}^{0}_{29}$	\overline{Q}_{30}	$\overline{Q}{}^{0}_{31}$	q ⁰ ₃₁
Latch	Н	Х	Н	Χ	L	$\overline{\mathbb{Q}}_{1}^{0}$	\overline{Q}^{0}_{2}	\overline{Q}^{0}_{3}	\overline{Q}_{4}^{0}	$\overline{Q}{}^{0}_{5}$	\overline{Q}_{6}^{0}	$\overline{\mathbb{Q}}_{7}^{0}$	\overline{Q}_8^0	$\overline{Q}{}^{0}_{9}$	Q ₀ 10	$\overline{\mathbb{Q}}^0_{11}$	Q ₀₁₂	\overline{Q}^{0}_{13}	Q ₀ 14	\overline{Q}^{0}_{15}	\overline{Q}^0_{16}	$\overline{Q}{}^{0}_{17}$	Q0 ₁₈	$\overline{Q}{}^{0}_{19}$	$\overline{Q}{}^{0}_{20}$	\overline{Q}^0_{21}	\overline{Q}^{0}_{22}	\overline{Q}^{0}_{23}	$\overline{Q}{}^{0}_{24}$	$\overline{Q}{}^{0}_{25}$	$\overline{Q}{}^{0}_{26}$	$\overline{Q}{}^{0}_{27}$	$\overline{Q}{}^{0}_{28}$	$\overline{Q}{}^{0}_{29}$	$\overline{Q}{}^{0}_{30}$	$\overline{Q}{}^{0}_{31}$	$\overline{Q}{}^{0}_{32}$	q ₃₂
Output disable	Х	Х	Х	Х	Н	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	Z	q ₃₂

Note

- ↑: Transition from low-to-high-level.
- $\overline{\mathbf{Q}}^0\!\!:$ Shows the status of output $\overline{\mathbf{Q}}$ before CK input changes.
- X: Irrelevant
- q⁰: The content of shift register before CK changes.
- q: The content of the shift register.
- Z: High-impedance state.

Absolute Maximum Ratings

 $(Ta = -40 \text{ to } +85^{\circ}\text{C}, \text{ unless otherwise noted})$

Item		Symbol	Ratings	Unit	Conditions
Supply voltage		Vcc	-0.5 to + 7.0	V	
Input voltage		Vı	-0.5 to $V_{CC} + 0.5$	V	
Output voltage	Vo	-0.5 to $V_{CC} + 0.5$	V		
Input protection diode current	I _{IK}	-20	mA	$V_{I} < 0 \ V$	
			20		$V_{I} > V_{CC}$
Output parasitic diode current	I _{OK}	-20	mA	V _O < 0 V	
			20		Vo > Vcc
Output current	$\overline{\mathbb{Q}}_1$ to $\overline{\mathbb{Q}}_{32}$	lo	50	mA	
	SQ ₃₂		±25		
Supply/GND current	Icc	-920, +20	mA	V _{CC} , GND	
Power dissipation	Pd	650	mW		
Storage temperature range		Tstg	-65 to +150	°C	

Recommended Operating Conditions

Item	Symbol	Min	Тур	Max	Unit
Supply voltage	V _{CC}	4.5	5	5.5	V
Input voltage	VI	0	_	V _{CC}	V
Output voltage	Vo	0	_	V _{CC}	V
Operating free-air ambient temperature	Topr	-40	_	+85	°C
range					

Electrical Characteristics

 $(V_{CC} = 4.5 \text{ to } 5.5 \text{ V}, \text{ unless otherwise noted})$

					Limits						
			7	Γa = 25°0	C	Ta = -40	to +85°C				
ltem		Sym bol	Min Typ		Max	Min	Max	Unit	Conditions		
Positive-going threshold voltage		V_{T+}	0.35×V _{CC}	2.8	0.7×V _{CC}	0.35×V _{CC}	0.7×V _{CC}	V	$V_O = 0.1V, V$ $ I_O = 20\mu A$		
Negative-going threshold voltage		V _{T-}	0.2×V _{CC}	2	0.55×V _{CC}	0.2×V _{CC}	0.55×V _{CC}	V	$V_O = 0.1V, V_O$ $ I_O = 20\mu A$	-	
High-level output	SQ ₃₂	V _{OH}	V _{CC} -0.1	_	_	V _{CC} -0.1	_	V	$\begin{aligned} V_I &= V_{T+}, V_{T-} \\ V_{CC} &= 4.5 V \end{aligned}$	I _{OH} = -20μA	
voltage			3.83	_	_	3.66	_			$I_{OH} = -4mA$	
Low-level	\overline{Q}_1 to	V_{OL}			0.1	_	0.1	V	$V_I = V_{T+}, V_{T-}$	$I_{OL} = 20 \mu A$	
output	\overline{Q}_{32}		_	0.20	0.41	_	0.50		$V_{CC} = 4.5V$	$I_{OL} = 24mA$	
voltage			_	0.25	0.48	_	0.55 (Note 2)	4	C	$I_{OL} = 28mA$	
	SQ ₃₂		_		0.1	_	0.1)	$I_{OL} = 20 \mu A$	
			_		0.44	_	0.53			$I_{OL} = 4mA$	
High-level input current		I _{IH}	_	_	0.5	_	5.0	μА	$V_I = V_{CC}, V_{CC}$; = 5.5V	
Low-level input current		I _{IL}	1	_	-0.5	_	-5.0	μА	$V_I = GND, V_0$	_{CC} = 5.5V	
Maximum	\overline{Q}_1 to	lo			1.0	-	10.0	μΑ	$V_I = V_{T+}$	$V_{O} = V_{CC}$	
output leak current	\overline{Q}_{32}		_	_	-1.0	0,	-10.0		V_{T-} $V_{CC} = 5.5V$	$V_O = GND$	
Quiescent state dissipation current		I _{CC}	_	_	40.0	5	400.0	μА	$V_I = V_{CC}$, GN $V_{CC} = 5.5V$	D,	

Note: 1. All typical values are at $V_{CC} = 5 \text{ V}$, $Ta = 25^{\circ}\text{C}$

2. $Ta = -40 \text{ to } +70^{\circ}\text{C}$

Switching Characteristics

 $(V_{CC} = 5V)$

			Limits					(100 31)	
			,	Ta = 25°C		Ta = - +85			
Item		Symbol	Min	Тур	Max	Min	Max	Unit	Conditions
Maximum clock frequer	су	f _{max}	5	30	_	4		MHz	$C_L = 50 \text{ pF}$
Output enable time to low-level	CK- \overline{Q}_1 to \overline{Q}_{32} (Turned on)	t _{PZL}	_	35	150	_	200	ns	$R_L = 1 \text{ k}\Omega$ (Note 2)
Output disable time from low-level	$CK-\overline{Q}_1$ to \overline{Q}_{32} (Turned off)	t _{PLZ}	_	35	200		250	ns	
Low-to-high, high-to-	CK-SQ ₃₂	t _{PLH}	_	35	100	_	130	ns	
low output propagation time		t _{PHL}	_	40	100		130	ns	
Output enable time to low-level	\overline{S}_D -Q ₁ to \overline{Q}_{32} (Turned on)	t _{PZL}	_	35	150		200	ns	
Low-to-high output propagation time	S _D -SQ ₃₂	t _{PLH}	_	40	100	_	130	ns	
Output enable time to low-level	$\overline{\text{LE}}$ - \overline{Q}_1 to \overline{Q}_{32} (Turned on)	t _{PZL}	_	30	100	-3	130	ns	
Output disable time from low-level	$\overline{\text{LE}}$ - $\overline{\mathbb{Q}}_1$ to $\overline{\mathbb{Q}}_{32}$ (Turned off)	t _{PLZ}	_	35	150	O	200	ns	
Output enable time to low-level	\overline{OE} - \overline{Q}_1 to \overline{Q}_{32} (Turned on)	t _{PZL}	_	30	100	_	130	ns	
Output disable time from low-level	\overline{OE} - \overline{Q}_1 to \overline{Q}_{32} (Turned off)	t _{PLZ}	_	35	150	_	200	ns	
Input capacitance		Cı		3	10		10	pF	
Output capacitance	Co		6	15	_	15	pF	OE-V _{CC}	
Power dissipation capa	citance (Note 1)	C _{PD}	40	160		_	_	pF	

Note 1. C_{PD} is the equivalent capacitance of IC calculated by the operating power dissipation without load. The operating power dissipation without load is given as follows.

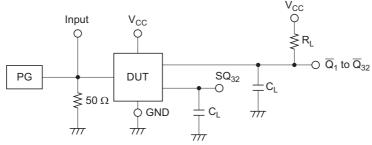
$$P_D = C_{PD} \bullet V_{CC}^2 \bullet f_I + I_{CC} \bullet V_{CC}$$

Timing Requirements

 $(V_{CC} = 5V)$

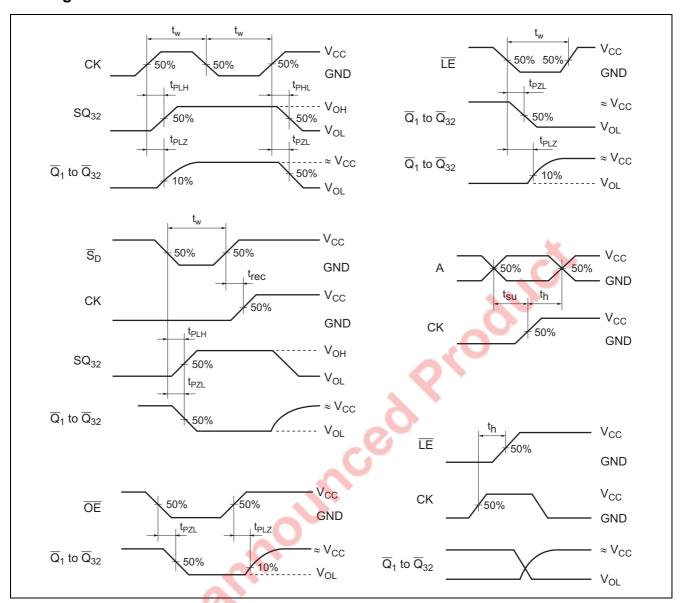
		Limits						
			Ta = 25°C		Ta = -40	to +85°C		
Item	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions
\overline{CK} , \overline{LE} , \overline{S}_D pulse width	t _W	100	16	_	130	_	ns	(Note 2)
Setup time A to CK	t _{su}	100	27	_	130	_	ns	
Hold time A to CK	th	10	5	_	15	_	ns	
Hold time LE to CK		50	15	_	70	_		
Recovery time CK to \overline{S}_D	t _{rec}	50	20	_	70	_	ns	

Note: 2. Test Circuit

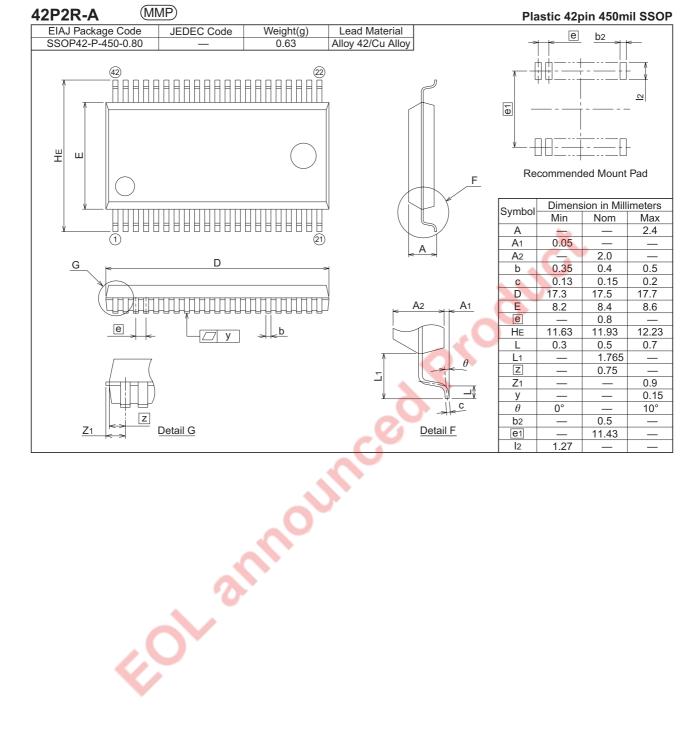


- (1) Characteristics of pulse generator (PG): tr = 6 ns, tf = 6 ns
- (2) C_L includes probe and stray capacitance.

Timing Chart



Package Dimensions



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